

Technical Data Sheet

Opto Interrupter

ITR9909-R

Features

- Fast response time
- High analytic
- Cut-off visible wavelength $\lambda_p=840\text{nm}$
- High sensitivity

Descriptions

The **ITR9909-R** consist of an infrared emitting diode and an NPN silicon phototransistor, encased side-by-side on converging optical axis in a black Thermoplastic

Housing The phototransistor receives radiation from the IRED only .This is the normal Situation. But when an object is in between , phototransistor could not receives the radiation. For additional component information , please refer to IR8294 and PT8294-6B-R

Applications

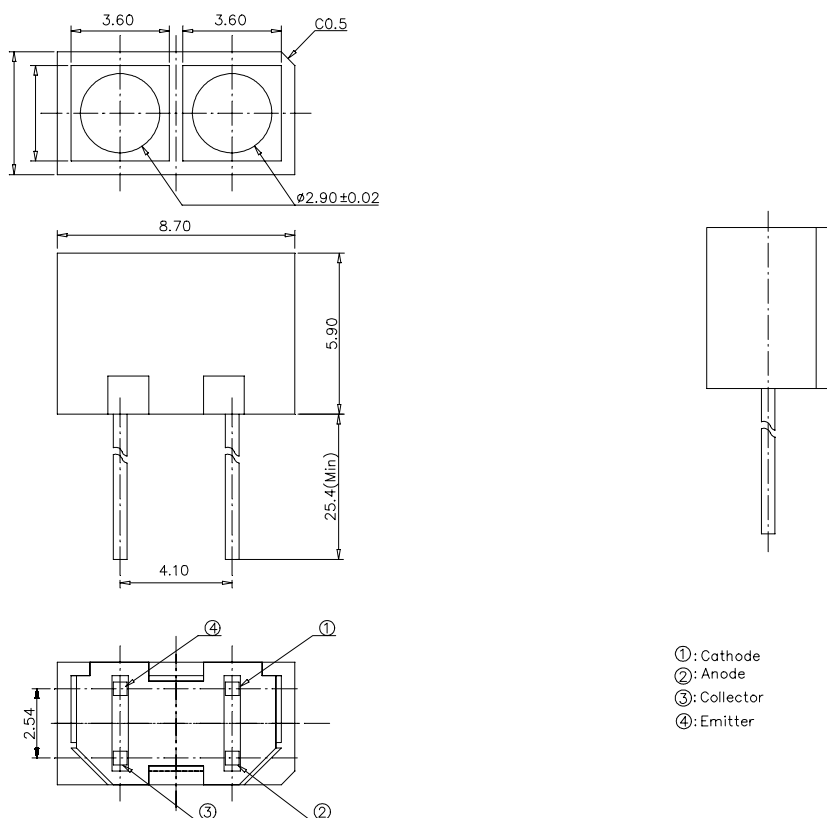
- Mouse Copier
- Switch Scanner
- Floppy disk driver
- Non-contact Switching
- For Direct Board

Device Selection Guide

Device No.	Chip Material	LENS COLOR
IR	GaAlAs	Blue
PT	Silicon	Black



Package Dimensions



Notes:

1. All dimensions are in millimeters
2. Tolerances unless dimensions ± 0.2 mm
3. Lead spacing is measured where the lead emerge from the package
4. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification
5. These specification sheets include materials protected under copyright of EVERLIGHT corporation . Please don't reproduce or cause anyone to reproduce them without EVERLIGHT's consent
6. When using this product , please observe the absolute maximum ratings and the instructions for use outlined in these specification sheets. EVERIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets

Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Ratings	Unit
Input	Power Dissipation at(or below) 25°C Free Air Temperature	Pd	100	mW
	Reverse Voltage	V _R	5	V
	Forward Current	I _F	50	mA
	Peak Forward Current (*1) Pulse width ≤ 100 μs, Duty cycle=1%	I _{FP}	1	A
Output	Collector Power Dissipation	P _C	75	mW
	Collector Current	I _C	50	mA
	Collector-Emitter Voltage	B V _{CEO}	30	V
	Emitter-Collector Voltage	B V _{ECO}	5	V
Operating Temperature		T _{opr}	-25~+85	°C
Storage Temperature		T _{stg}	-40~+85	°C
Lead Soldering Temperature (*2) (1/16 inch form body for 5 seconds)		T _{sol}	260	°C

(*1) $t_w=100 \mu \text{sec.}$, $T=10 \text{ msec.}$ (*2) $t=5 \text{ Sec}$

Electro-Optical Characteristics (Ta=25°C)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Conditions
Input	Forward Voltage	V _{F1}	---	1.2	1.5	V	I _F =20mA
		V _{F2}	---	1.4	1.85		I _F =100mA, tp=100 μs, tp/T=0.01
		V _{F3}	---	2.6	4.0		I _F =1A, tp=100 μs, tp/T=0.01
	Reverse Current	I _R	---	---	10	μA	V _R =5V
	Peak Wavelength	λ _p	---	940	---	nm	I _F =20mA
	View Angle	2θ1/2	---	110	---	Deg	I _F =20mA
Output	Dark Current	I _{CEO}	---	---	100	nA	V _{CE} =20V, Ee=0mW/cm ²
	C-E Saturation Voltage	V _{CE(sat)}	---	---	0.4	V	I _C =2mA , Ee=1mW/cm ²
Transfer Characteristics	Collect Current	I _{C(ON)}	0.2	---	---	mA	V _{CE} =5V
	Leakage Current	I _{CEOD}	---	---	1	μA	I _F =20mA
	Rise time	t _r	---	15	---	μsec	V _{CE} =5V
	Fall time	t _f	---	15	---	μsec	I _C =1mA R _L =1KΩ

ITR9909-R

Typical Electrical/Optical/Characteristics Curves for IR

Fig. 1 Forward Current vs. Ambient Temperature

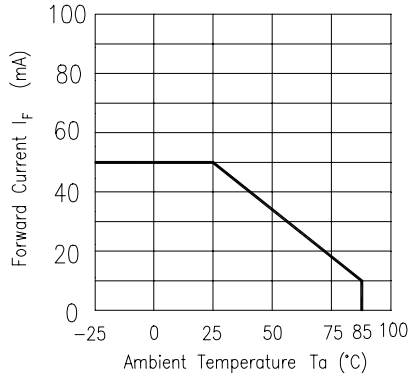


Fig. 2 Spectral Distribution

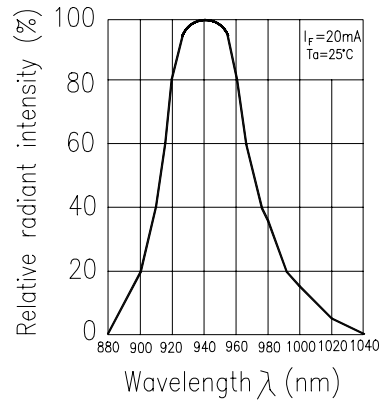


Fig. 3 Peak Emission Wavelength vs. Ambient Temperature

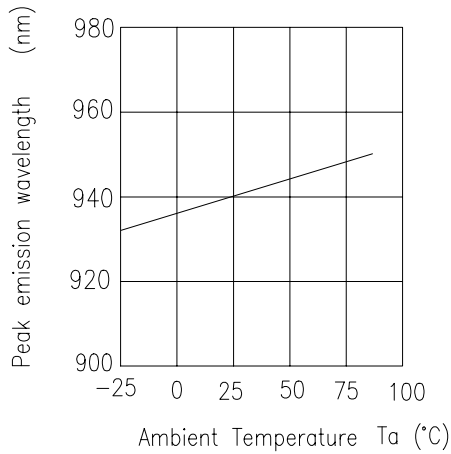


Fig. 4 Forward Current vs. Forward Voltage

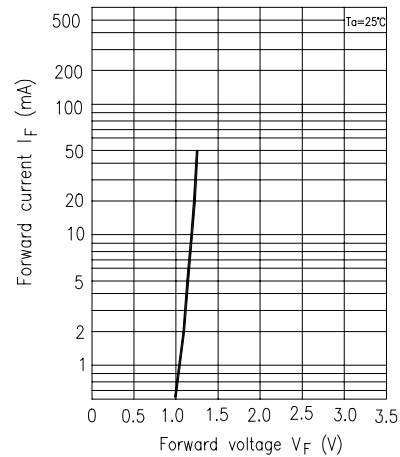


Fig. 5 Forward Voltage vs. Ambient Temperature

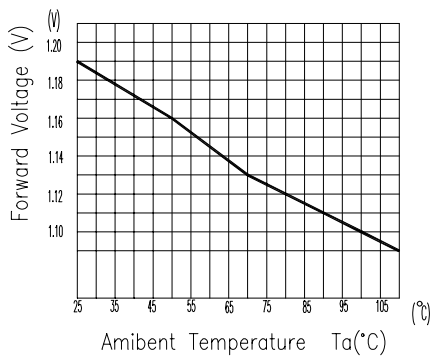
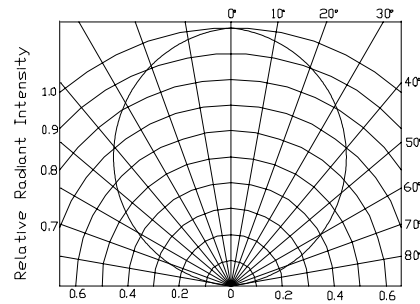


Fig. 6 Relative Radiant Intensity vs. Angular Displacement



Typical Electrical/Optical/Characteristics Curves for PT

Fig.1 Collector Power Dissipation vs. Ambient Temperature

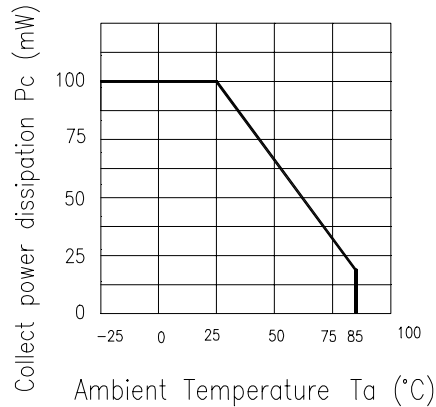


Fig.2 Collector Dark Current vs. Ambient Temperature

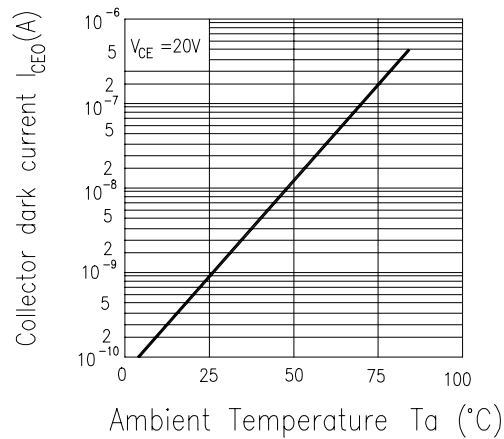


Fig. 3 Relative Collector Current vs. Ambient Temperature

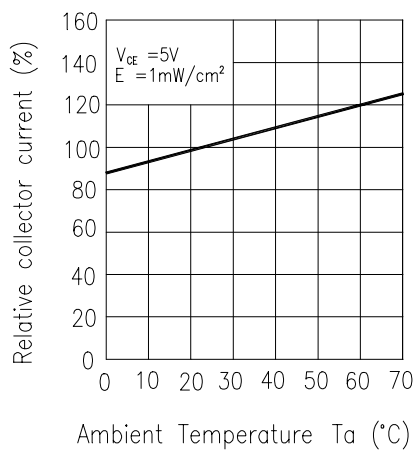


Fig.4 Collector Current vs. Irradiance

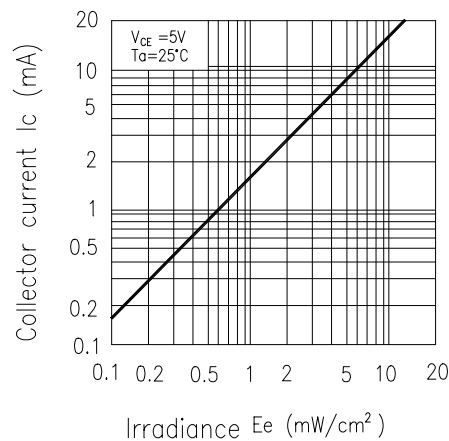


Fig.5 Spectral Sensitivity

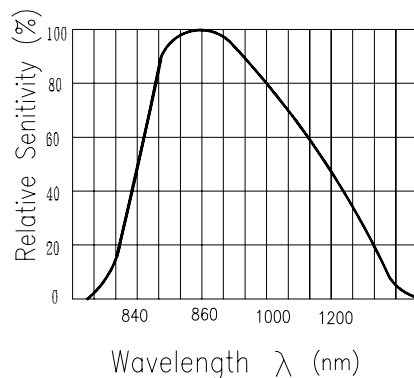
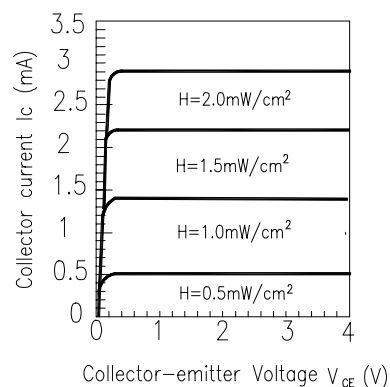


Fig.6 Collector Current vs. Collector-emitter Voltage



Reliability Test Item And Condition

The reliability of products shall be satisfied with items listed below.

Confidence level : 90%

LTPD : 10%

NO.	Item	Test Condition	Test Hours/ Cycle	Sample Size	Failure Judgement Criteria	Ac/Re
1	Solder Heat	TEMP : 260°C ± 5 °C	5 sec	22 PCs	More than 90% of lead to be covered by soldering	0/1
2	Temperature Cycle	H : +85°C 30 mins 5 min L : -55°C 30 min	50 cycle	22 PCs	$I_R \geq U \times 2$ $E_e \leq L \times 0.8$ $V_F \geq U \times 1.2$	0/1
3	Thermal Shock	H : +100°C 5 min 10 sec L : -10°C 5 min	50 cycle	22 PCs	U : Upper specification limit L : Lower specification limit	0/1
4	High Temperature Storage	TEMP. : +100°C	1000 hrs	22 PCs		0/1
5	Low Temperature Storage	TEMP. : -55°C	1000 hrs	22 PCs		0/1
6	DC Operating Life	V _{CE} =5V I _F =20mA	1000 hrs	22 PCs		0/1
7	High Temperature / High Humidity	85°C / 85% R.H.	1000 hrs	22 PCs		0/1

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